

argon.

Sub B2  
A1  
3. (Amended) The method of claim 2, wherein hydrogen is provided to the processing chamber in a helium and hydrogen mixture of about 95% helium by volume and about 5% hydrogen by volume.

4. (Amended) The method of claim 1, wherein an etch rate increases when helium content [is increased] increases.

5. The method of claim 1, wherein the substrate surface comprises silicon oxide or silicon nitride.

HE  
6. The method of claim 1, wherein the plasma is capacitively and inductively powered.

Sub B3  
A2  
7. (Amended) The method of claim 1, wherein argon, helium and hydrogen are introduced into the processing chamber [is maintained at] to establish a pressure from about 1 mTorr to about 200 mTorr.

Sub B3  
8. (Amended) A method for processing a substrate, comprising:

(a) exposing a patterned substrate surface to a plasma comprising argon, helium and hydrogen in a [reaction] processing chamber; and

(b) increasing the helium content of the plasma to increase etching of the patterned substrate surface.

HE  
9. The method of claim 8, wherein the plasma comprises less than about 75% by volume of argon.

Sub B4  
A3  
10. (Amended) The method of claim 9, wherein hydrogen is provided to the [reaction] processing chamber in a helium and hydrogen mixture of about 95% helium by volume and about 5% hydrogen by volume.

NE 11. The method of claim 8, wherein the substrate surface comprises silicon oxide or silicon nitride.

12. The method of claim 8, wherein the plasma is capacitively and inductively powered.

Sub C10  
A4 13. (Amended) The method of claim 1, wherein [the reaction chamber is maintained at] argon, helium and hydrogen are introduced into the processing chamber to establish a pressure from about 1 mTorr to about 200 mTorr.

14. (Amended) A method for processing a substrate, comprising:

(a) exposing a patterned substrate surface to a plasma comprising argon, helium and hydrogen in a [reaction] processing chamber, wherein the plasma is capacitively and inductively powered; and

(b) increasing the helium content of the plasma to increase [cleaning] etching of the patterned substrate surface, wherein the plasma comprises less than about 75% by volume of argon.

Sub B5 15. (Amended) The method of claim 14, wherein hydrogen is provided to the [reaction] processing chamber in a helium and hydrogen mixture of about 95% helium by volume and about 5% hydrogen by volume.

NE 16. The method of claim 15, wherein the substrate surface comprises silicon oxide or silicon nitride.

Sub C10  
A5 17. (Amended) The method of claim 14, wherein [the reaction chamber is maintained at] argon, helium and hydrogen are introduced into the processing chamber to establish a pressure from about 1 mTorr to about 200 mTorr.

Please add new claims 18-23 as follows: ✓